CLAIMS

1. A CVD apparatus for forming a film on a substrate by a CVD method, the apparatus comprising:

a chamber;

a substrate holder that is disposed in the chamber and holds the substrate; and

a gas introduction mechanism that introduces raw material gas into the chamber,

wherein a film formed of ~~any~~ material ~~of metal, ceramics, plastic and cermet~~ is formed on at least one of an inner surface of the chamber, the substrate holder, an adhesion-preventing plate disposed in the chamber, a jig disposed in the chamber and a gas shower member that introduces the raw material gas into the chamber in a shower state,

wherein the material contains Cr in an amount of 1% by weight or more to 50% by weight or less, WC in an amount of 30% by weight or more to 40% by weight or less, Mo in an amount of 0% by weight or more to 49% by weight or less, Cr, WC and Mo in an amount of 50% by weight or less in total, Fe, Si, C, B, Al and Cu in an amount of 0% by weight or more to 50% by weight or less in total, and a residue includes Ni and unavoidable impurity.

~~2. The CVD apparatus according to claim 1,~~

~~wherein the material contains at least one of Cr, W and Mo in an amount of 10% by weight or more.~~

~~3. The CVD apparatus according to claim 1 or 2, wherein the material contains Cr in an amount of 1% by weight or more to 50% by weight or less, WC in an amount of 0% by weight or more to 49% by weight or less, Mo in an amount of 0% by weight or more to 49% by weight or less, Cr, WC and Mo in an amount of 50% by weight or less in total, Fe, Si, C, B, Al and Cu in an amount of 0% by weight or more~~

~~to 50% by weight or less in total, and a residue includes Ni and unavoidable impurity.~~

2. A CVD apparatus for forming a film on a substrate by a CVD method, the apparatus comprising:

a chamber;

a substrate holder that is disposed in the chamber and holds the substrate; and

a gas introduction mechanism that introduces raw material gas into the chamber,

wherein a film formed of material is formed on at least one of an inner surface of the chamber, the substrate holder, an adhesion-preventing plate disposed in the chamber, a jig disposed in the chamber and a gas shower member that introduces the raw material gas into the chamber in a shower state,

wherein the material contains Cr in an amount of 1% by weight or more to 50% by weight or less, WC in an amount of 0% by weight or more to 49% by weight or less, Mo in an amount of 3% by weight or more to 10% by weight or less, Cr, WC and Mo in an amount of 50% by weight or less in total, Fe, Si, C, B, Al and Cu in an amount of 0% by weight or more to 50% by weight or less in total, and a residue includes Ni and unavoidable impurity,

wherein the film including the material is formed by heat spraying.

~~4~~3. The CVD apparatus according to claim ~~3~~1 or 2,

wherein the material contains the Fe in an amount of 0% by weight or more to 10% by weight or less, the Si in an amount of 0% by weight or more to 10% by weight or less, the C in an amount of 0% by weight or more to 3% by weight or less, the B in an amount of 0% by weight or more to 7% by weight or less, the Al in an amount of 0% by weight or more to 15% by weight or less and the Cu in an amount of 0% by weight or more to 5% by weight or less.

~~5~~4. The CVD apparatus according to ~~claim 3 or 4~~any one of claims 1 to 3,

wherein the material contains Cr in an amount of 9% by weight or more to 20% by weight or less.

~~6~~5. The CVD apparatus according to ~~any one of claims 3 to 5~~claim 1,

wherein the material contains Mo in an amount of 3% by weight or more to 10% by weight or less.

~~7~~6. The CVD apparatus according to ~~any one of claims 3 to 6~~claim 2,

wherein the material contains WC in an amount of 30% by weight or more to 40% by weight or less.

~~8. The CVD apparatus according to claim 2,~~

~~wherein the material contains Mo in an amount of 80% by weight or more, and a residue includes an impurity and an unavoidable impurity.~~

~~9. The CVD apparatus according to claim 8,~~

~~wherein the impurity is at least one of Fe, Si and C.~~

~~10~~7. The CVD apparatus according to ~~any one of claims 1 to 9~~claim 1,

wherein the film including the material is formed by heat spraying.

~~11~~8. The CVD apparatus according to any one of claims 1 to ~~10~~7,

wherein the film to be formed on the substrate is a carbon film.